

Silicon NPN Power Transistors

2SC2608

DESCRIPTION

- With TO-3 package
- Complement to type 2SA1117
- High power dissipation

APPLICATIONS

- For power amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

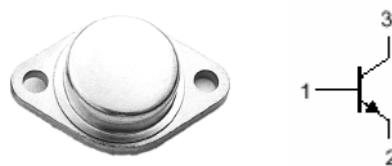


Fig.1 simplified outline (TO-3) and symbol

ABSOLUTE MAXIMUM RATINGS($T_c=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	200	V
V_{CEO}	Collector-emitter voltage	Open base	200	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		17	A
P_C	Collector power dissipation	$T_c=25^\circ\text{C}$	200	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=25mA ; I_B=0$	200			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=1mA ; I_E=0$	200			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA ; I_C=0$	6			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C=8A ; I_B=0.8A$			2.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=200V ; I_E=0$			0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=6V ; I_C=0$			0.1	mA
h_{FE}	DC current gain	$I_C=8A ; V_{CE}=4V$	20			
f_T	Transition frequency	$I_C=1A ; V_{CE}=12V$		20		MHz

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PACKAGE OUTLINE

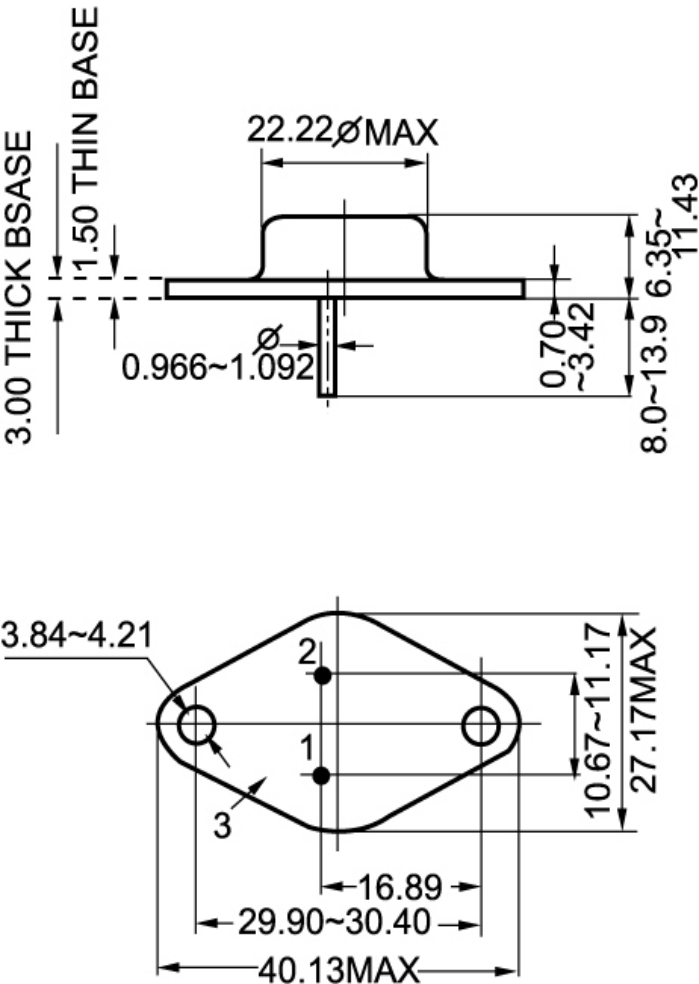


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)